



# STW77N65M5

N-channel 650 V, 0.033  $\Omega$ , 69 A, MDmesh™ V Power MOSFET  
TO-247

## Features

Order code	$V_{DSS}$ @ $T_{jmax.}$	$R_{DS(on)}$ max.	$I_D$
STW77N65M5	710 V	< 0.038 $\Omega$	69 A

- Higher  $V_{DSS}$  rating
- Higher dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

## Application

Switching applications

## Description

This device is a N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

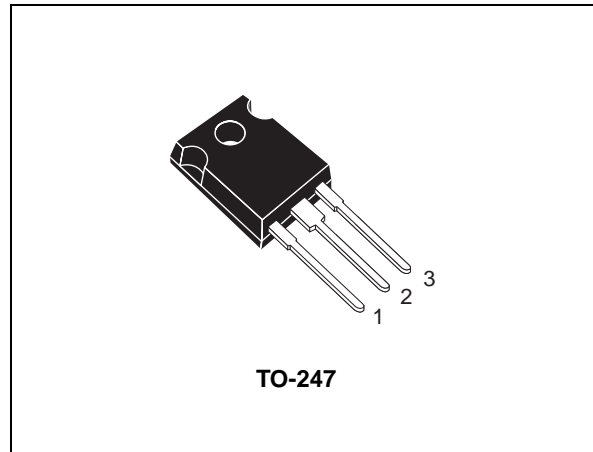


Figure 1. Internal schematic diagram

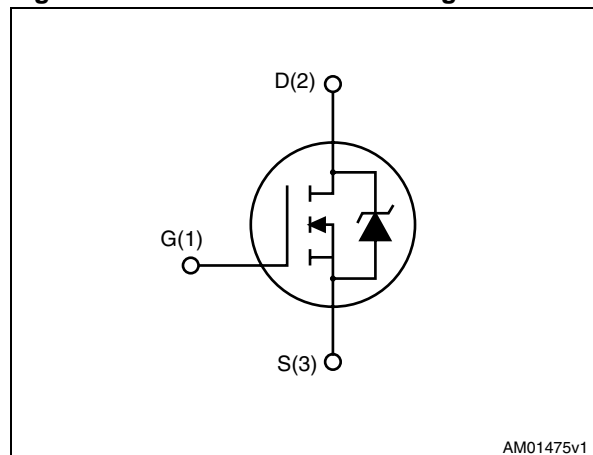


Table 1. Device summary

Order code	Marking	Package	Packaging
STW77N65M5	77N65M5	TO-247	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	25	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	69	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	41.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	276	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	400	W
$I_{AR}$	Max current during repetitive or single pulse avalanche (pulse width limited by $T_{JMAX}$ )	15	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	2000	mJ
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	°C
$T_j$	Max. operating junction temperature	150	°C

1. Pulse width limited by safe operating area

2.  $I_{SD} \leq 69\text{ A}$ ,  $di/dt = 400\text{ A}/\mu\text{s}$ , peak  $V_{DS} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.31	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	°C/W
$T_l$	Maximum lead temperature for soldering purpose	300	°C

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 34.5\text{ A}$		0.033	0.038	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	9800	-	pF
$C_{oss}$	Output capacitance			200		pF
$C_{rss}$	Reverse transfer capacitance			6		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	590	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	194	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.2	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 34.5\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 16</a> )	-	185	-	nC
$Q_{gs}$	Gate-source charge			45		nC
$Q_{gd}$	Gate-drain charge			65		nC

- $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(V)}$	Voltage delay time	$V_{DD} = 400\text{ V}$ , $I_D = 40\text{ A}$ ,		160		ns
$t_{r(V)}$	Voltage rise time	$R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$		22		ns
$t_{f(i)}$	Current fall time	(see <a href="#">Figure 17</a> )	-	20	-	ns
$t_{c(off)}$	Crossing time	(see <a href="#">Figure 20</a> )		40		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				69	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		276	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 69\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 69\text{ A}$ ,		570		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$	-	14		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$V_{DD} = 100\text{ V}$ (see <a href="#">Figure 17</a> )		48		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 69\text{ A}$ ,		700		ns
$Q_{rr}$	Reverse recovery charge	$di/dt = 100\text{ A}/\mu\text{s}$	-	20		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 17</a> )		58		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

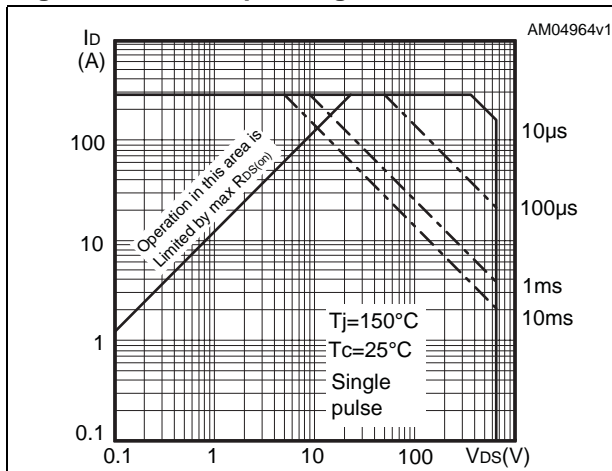


Figure 3. Thermal impedance

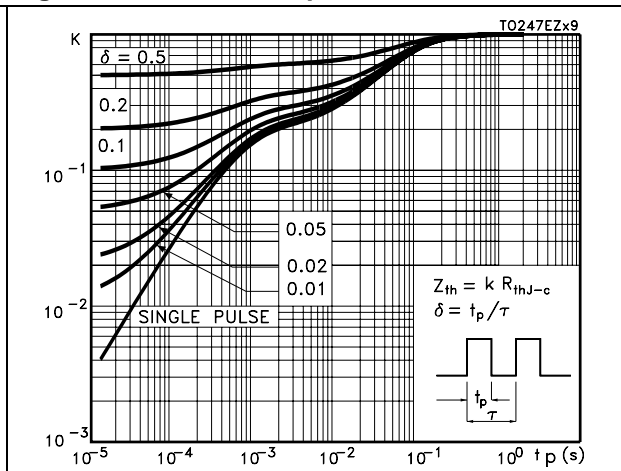


Figure 4. Output characteristics

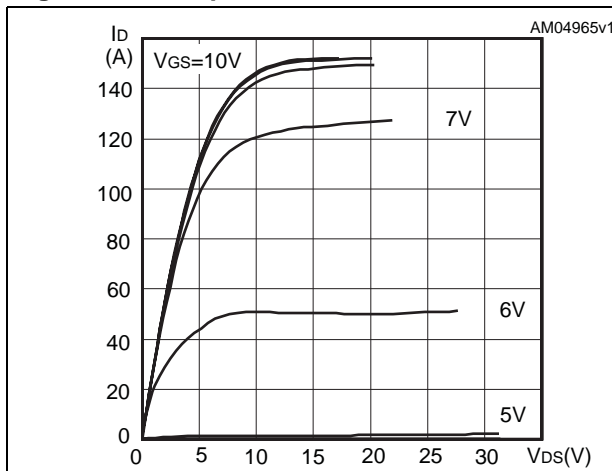


Figure 5. Transfer characteristics

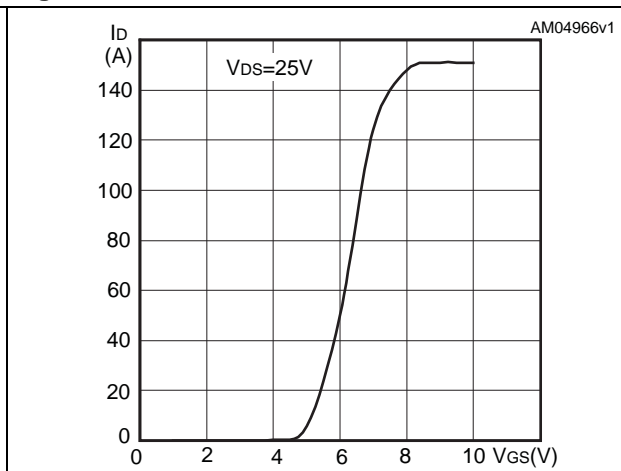


Figure 6. Gate charge vs gate-source voltage

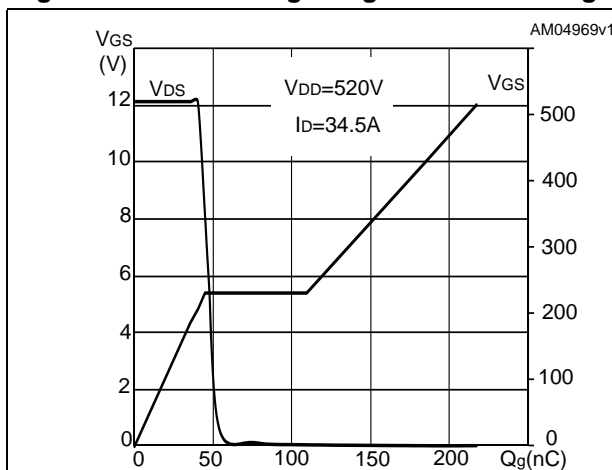


Figure 7. Static drain-source on resistance

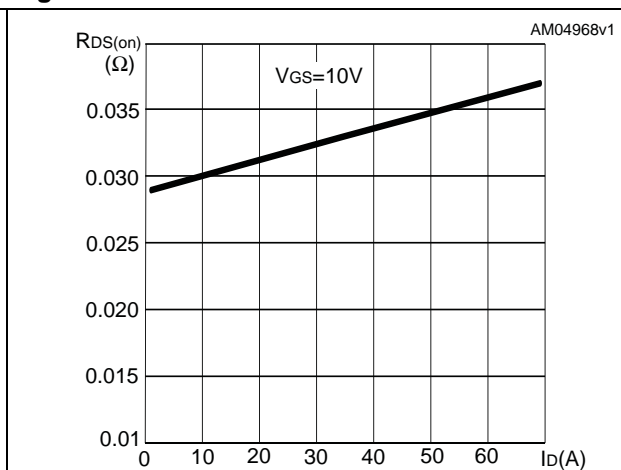


Figure 8. Capacitance variations

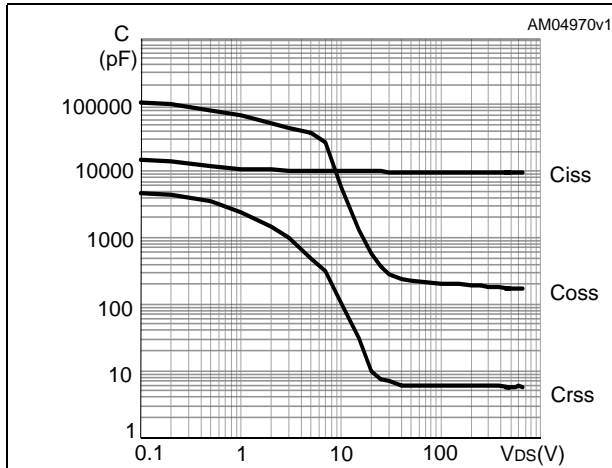


Figure 9. Output capacitance stored energy

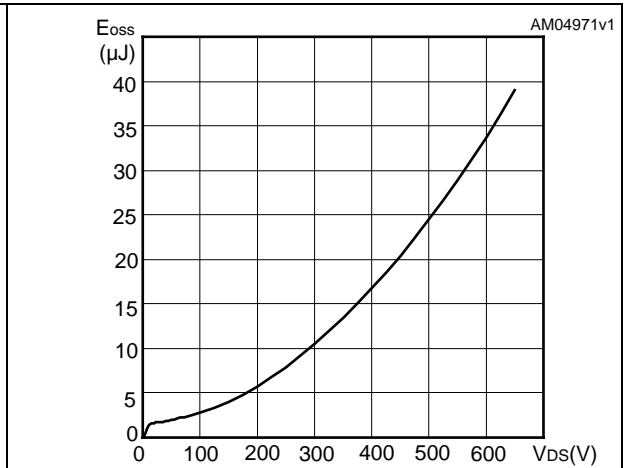


Figure 10. Normalized gate threshold voltage vs temperature

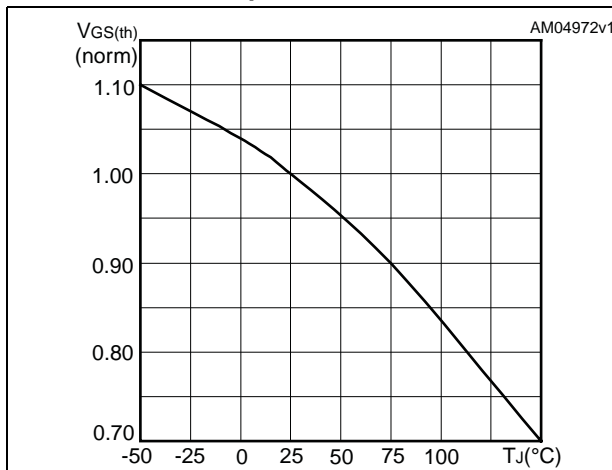


Figure 11. Normalized on resistance vs temperature

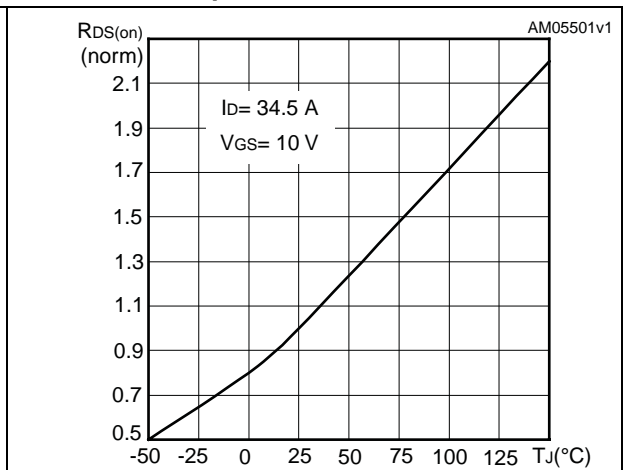


Figure 12. Source-drain diode forward characteristics

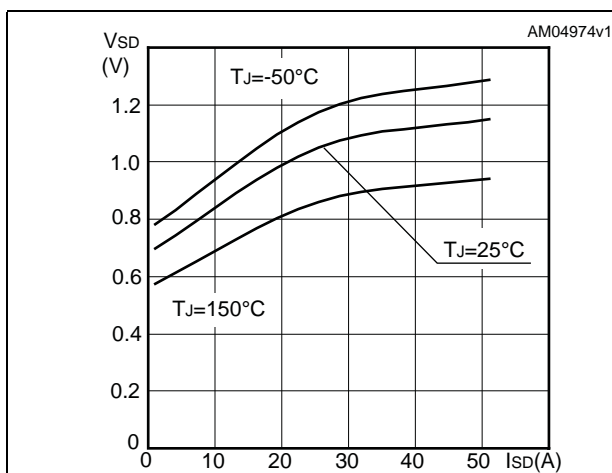


Figure 13. Normalized B<sub>VDS</sub> vs temperature

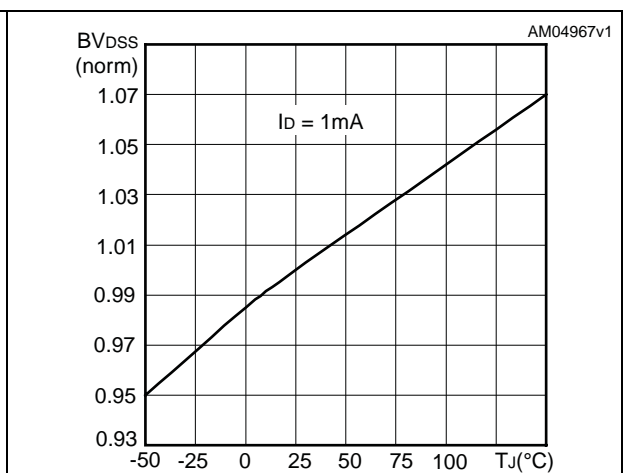
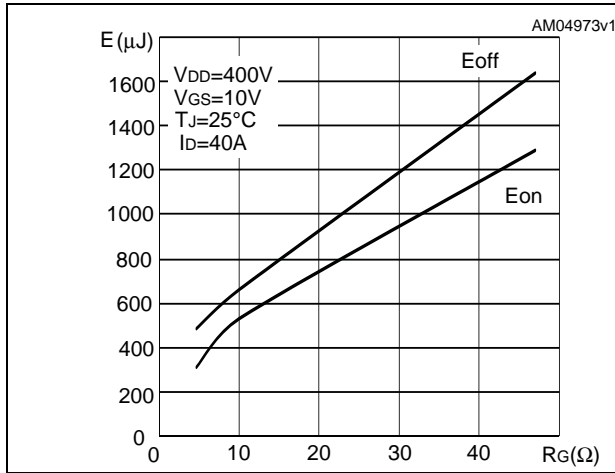


Figure 14. Switching losses vs gate resistance (1)

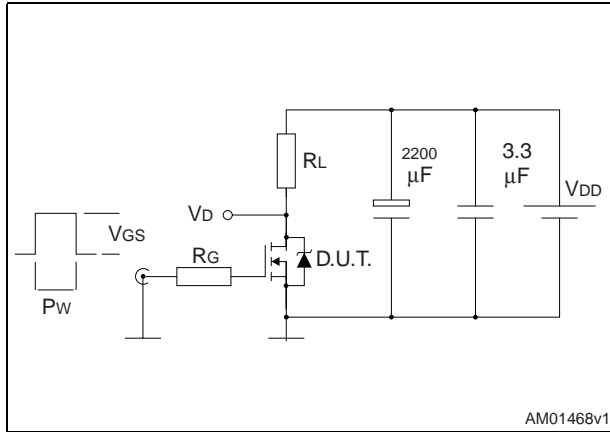


1.  $E_{\text{on}}$  including reverse recovery of a SiC diode



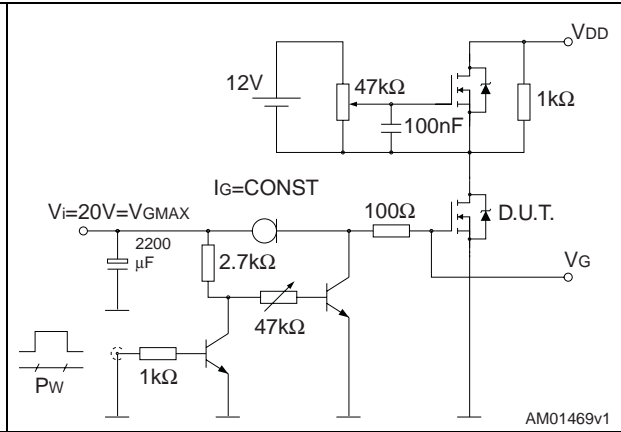
### 3 Test circuits

Figure 15. Switching times test circuit for resistive load



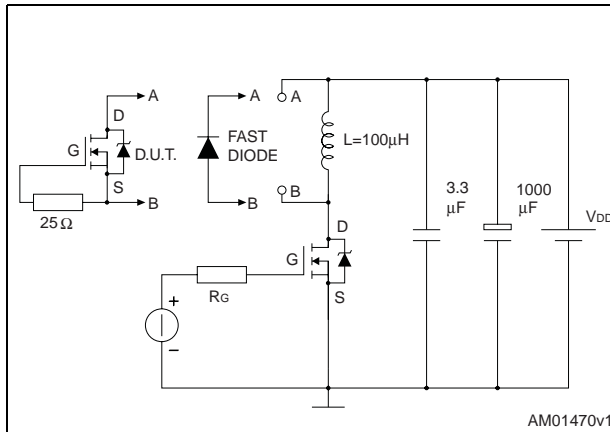
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Figure 16. Gate charge test circuit



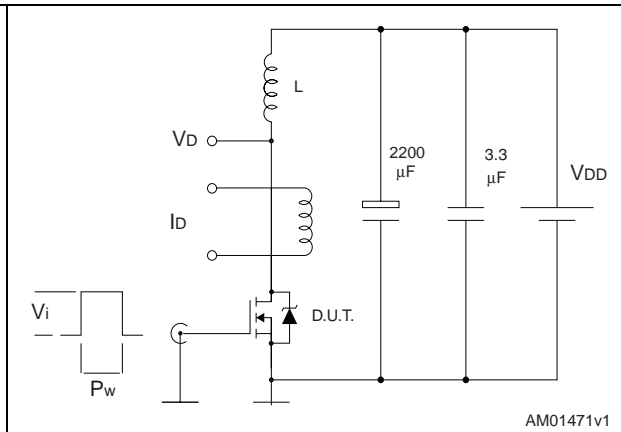
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Figure 17. Test circuit for inductive load switching and diode recovery times



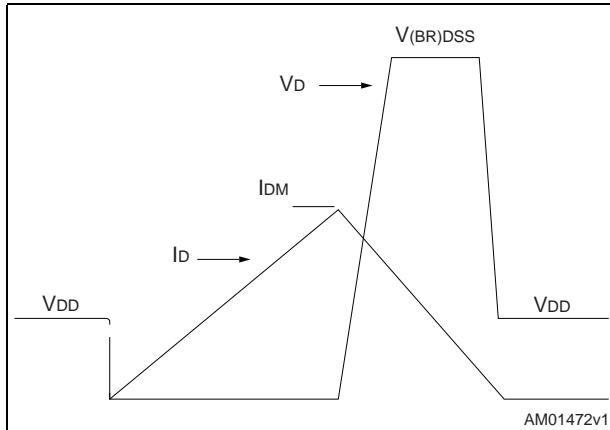
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Figure 18. Unclamped inductive load test circuit



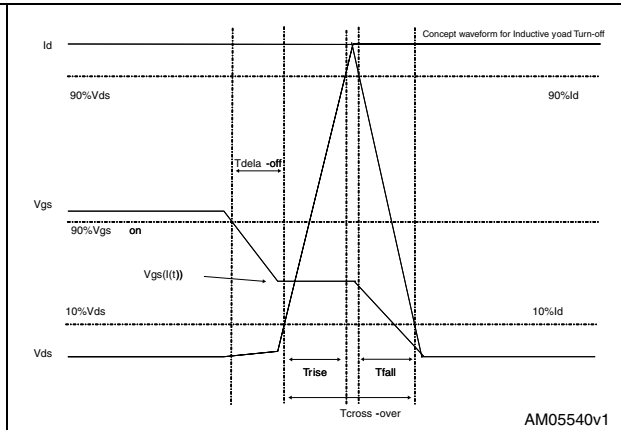
AM01471v1

Figure 19. Unclamped inductive waveform



AM01472v1

Figure 20. Switching time waveform



AM05540v1

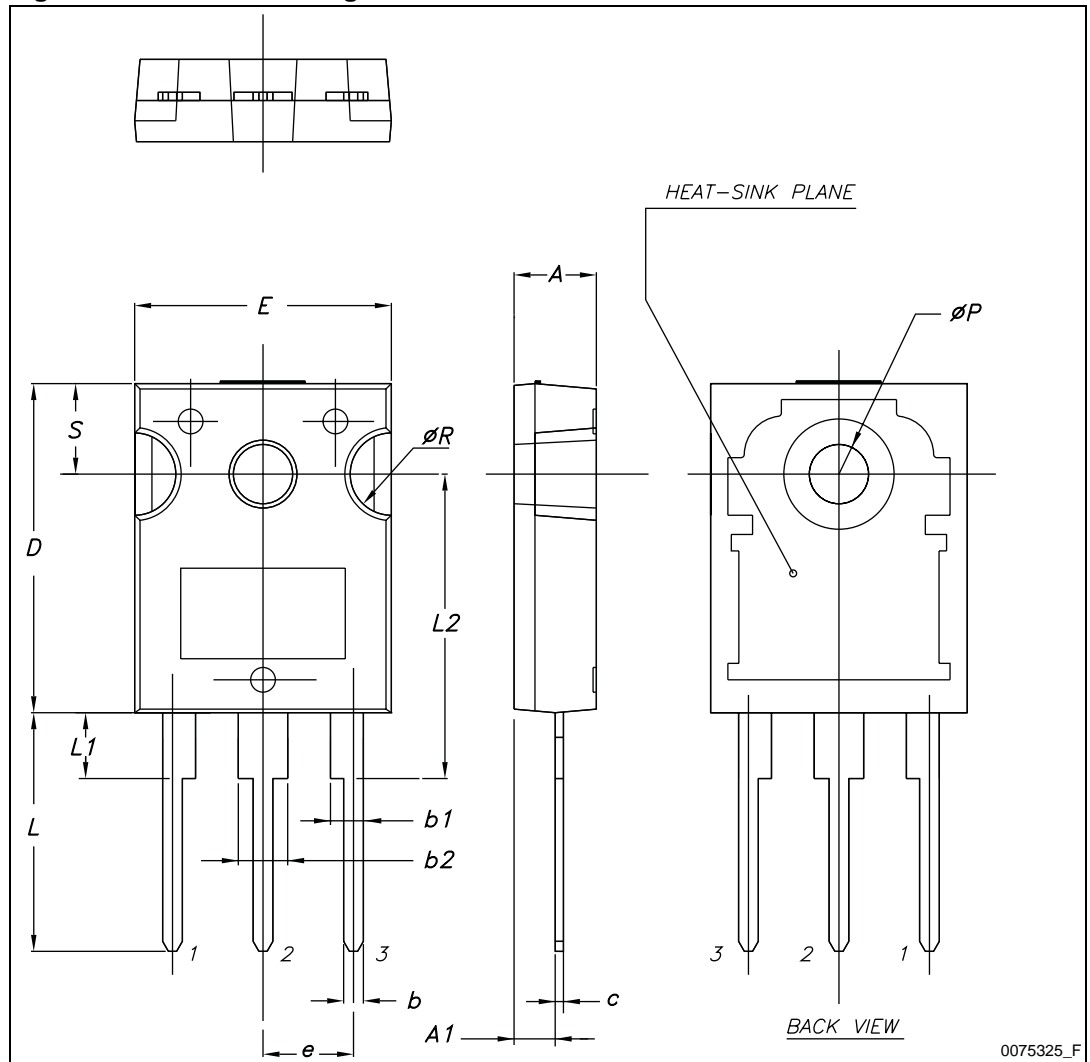
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 8. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 21. TO-247 drawing



0075325\_F

## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
20-Jan-2009	1	First release.
14-Jul-2009	2	Document status promoted from preliminary data to datasheet.
03-Feb-2011	3	<a href="#">Section 2.1: Electrical characteristics (curves)</a> has been updated.

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